

### General Description

The 65R105 is power MOSFET using Cmos's advanced super junction technology that can realize very low on resistance and gate charge. It will provide much high efficiency by using optimized charge coupling technology. These devices are well suited for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.

### Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

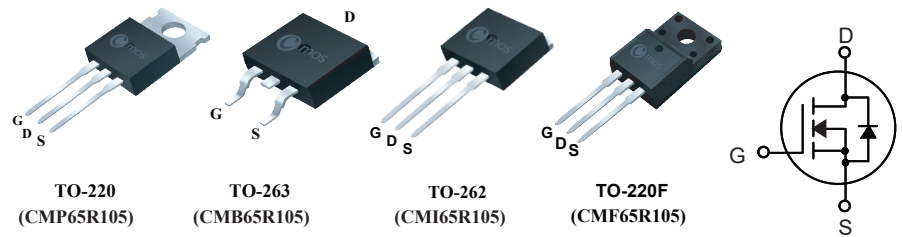
### Product Summary

BVDSS	R <sub>DS(on)</sub> max.	ID
650V	100mΩ	31A

### Applications

- Charger
- Adaptor
- Power Supply

### TO-220/263/262/220F Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	220/263/262	220F	Units
V <sub>DS</sub>	Drain-Source Voltage	650		V
V <sub>GS</sub>	Gate-Source Voltage	±30		V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current	31	31*	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current	20	20*	A
I <sub>DM</sub>	Pulsed Drain Current	124	124*	A
EAS	Single Pulse Avalanche Energy (Note 1)	1353		mJ
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation	250	40	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150		°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150		°C

\* Drain current limited by maximum junction temperature.

### Thermal Data

Symbol	Parameter	220/263/262	220F	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient Max.	64	64	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-case Max.	0.5	3.13	°C/W

### Electrical Characteristics (T<sub>J</sub>=25°C , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	650	---	---	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V , I <sub>D</sub> =15A	---	85	100	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	3	---	5	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =650V , V <sub>GS</sub> =0V	---	---	5	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V , V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V , I <sub>D</sub> =15A	---	14	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz	---	1.1	---	Ω
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =17A	---	57	---	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =480V	---	19.5	---	
Q <sub>gd</sub>	Gate-Drain Charge	V <sub>GS</sub> =10V	---	30	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DS</sub> =400V	---	63	---	ns
T <sub>r</sub>	Rise Time	V <sub>GS</sub> =10V	---	106	---	
T <sub>d(off)</sub>	Turn-Off Delay Time	I <sub>D</sub> =17A	---	132	---	
T <sub>f</sub>	Fall Time	R <sub>G</sub> =27Ω	---	30	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V , V <sub>GS</sub> =0V , f=1MHz	---	2200	---	pF
C <sub>oss</sub>	Output Capacitance		---	4120	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	350	---	

### Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	31	A
I <sub>SM</sub>	Pulsed Source Current		---	---	124	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =17A	---	0.91	1.4	V

Note :

1.The EAS data shows Max. rating .The test condition is V<sub>DS</sub>=80V , V<sub>GS</sub>=10V , L=30mH , I<sub>AS</sub>=9.5A.

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Typical Characteristics

